

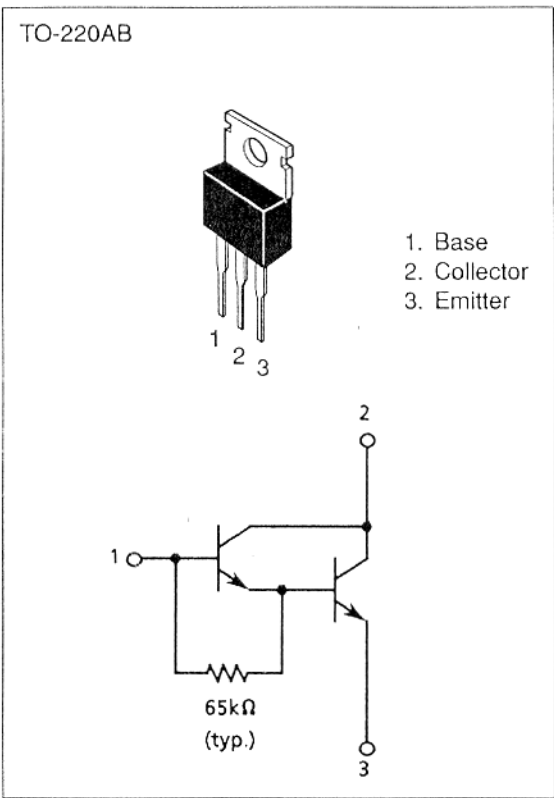
2SD1502

Silicon NPN Triple Diffused
Low Frequency Power Amplifier

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Rating	Unit
Collector to base voltage	V _{CBO}	300	V
Collector to emitter voltage	V _{CEO}	300	V
Emitter to base voltage	V _{EBO}	7	V
Collector current	I _C	0.3	A
Collector peak current	i _{C(peak)}	0.6	A
Collector power dissipation	P _C	1.5	W
	P _C ^{*1}	15	
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

Note: 1. Value at T_C = 25°C.



Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test condition
Collector to base breakdown voltage	V _{(BR)CBO}	300	—	—	V	I _C = 1 mA, I _E = 0
Collector to emitter breakdown voltage	V _{(BR)CEO}	300	—	—	V	I _C = 10 mA, R _{BE} = ∞
Emitter to base breakdown voltage	V _{(BR)EBO}	7	—	—	V	I _E = 1 mA, I _C = 0
Collector cutoff current	I _{CBO}	—	—	10	μA	V _{CB} = 300 V, I _E = 0
	I _{CEO}	—	—	10		V _{CE} = 60 V, R _{BE} = ∞
Emitter cutoff current	I _{EBO}	—	—	10	μA	V _{EB} = 5 V, I _C = 0
DC current transfer ratio	h _{FE1}	1000	—	—		V _{CE} = 1.5 V, I _C = 20 mA ^{*1}
	h _{FE2}	1500	—	—		V _{CE} = 1.5 V, I _C = 100 mA ^{*1}

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Electrical Characteristics (Ta = 25°C) (cont)

Item	Symbol	Min	Typ	Max	Unit	Test condition
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	1.5	V	$I_C = 100\text{ mA}, I_B = 0.2\text{ mA}^{*1}$
Base to emitter saturation voltage	$V_{BE(sat)}$	—	—	2.0	V	$I_C = 100\text{ mA}, I_B = 0.2\text{ mA}^{*1}$

Note: 1. Pulse Test.

